Refine Search Search Results -Documents Terms 1.3 and (barium adj strontium adj titanate) US Pru-Grant Publication Full-Text Database US OCR Full-Text Database Database: EPO Abstracts Database JPO Abstract, Dutabase Derwent World Patents Index IBM Technical Disclosure Bulletins L5 Refine Search Search: 5.-call Text ≢ Interrupt Clear Search History DATE: Saturday, June 26, 2004 Printable Copy Create Case

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<u>L5</u>	L3 and (barium asj strontic m adj titanate)	3	<u>L5</u>
<u>L4</u>	L3 and (metal near5 patterning)	6	<u>L4</u>
<u>L3</u>	L2 and refractory	21	<u>L3</u>
<u>L2</u>	L1 and (gate near electrosts)	48	<u>L2</u>
<u>L1</u>	(integrated adj circuit, and (silicon adj dioxide) and (water adj vapor) and (molybdenum or trangsten) and polycrystalline	110	<u>L1</u>

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Search Results - Record(s) 1 through 3 of 3 returned.

1. **Document ID**: US 6737341 B1

L5: Entry 1 of 3

File: USPT

May 18, 2004

US-PAT-NO: 6737341

DOCUMENT-IDENTIFIER: US 6737341 B1

TITLE: Semiconductor integrated circuit device and method for manufacturing the

same

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US-PAT-NO: 6593229

DOCUMENT-IDENTIFIER: US 6593229 B1

TITLE: Semiconductor integrated circuit device and method for manufacturing the

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☐ 3. Document ID: US 6482740 B2

L5: Entry 3 of 3

File: USPT

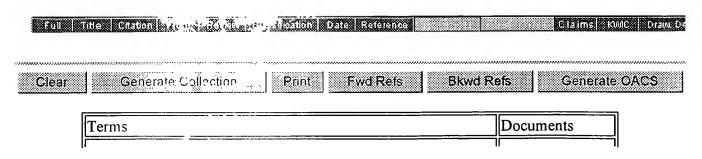
Nov 19, 2002

US-PAT-NO: 6482740

DOCUMENT-IDENTIFIER: US 6482740 B2

TITLE: Method of growing electrical conductors by reducing metal oxide film with

organic compound centaining -O: . -CHO, or -COOH



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L3 and (barium adi strontium adj titanate)

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US-PAT-NO: 6737341 DOCUMENT-IDENTIFIER: US COLVS41 B1		4
CITLE: Semiconductor <u>introducted singuit</u> device and method for manufacturame	ring the	
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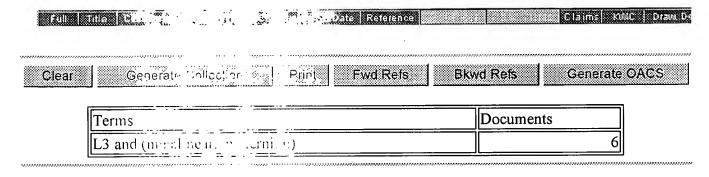
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same

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